

Amendments to the Specification are as follows:

Before the first sentence on page 1 please insert the following paragraph.

This application claims the benefit of priority to Japanese Patent Application No. 2003-110847, herein incorporated by reference.

Please amend the paragraph beginning on page 2, line 4 and ending on page 2, line 10 as follows:

The shape of the metal plate 4 is a square ~~15.24~~15.24 cm (6 inches) on a side. The distance between the metal plate 4 and the grounded surface 6 is defined so that the metal plate 4 and the grounded surface 6 form together a capacitor having a capacity of 20 pF with air used as its dielectric. Specifically, the distance between the metal plate 4 and the grounded surface 6 is approximately 2 cm.

Please amend the paragraph beginning on page 20, line 9 and ending on page 20, line 13 as follows:

The shape of the metal plate 4 is a square ~~15.24~~15.24 cm (6 inches) on a side. The distance between the metal plate 4 and the grounded surface 6 is defined so that the metal plate 4 and the grounded surface 6 form together a capacitor having a capacity of 20 pF with air used as its dielectric.

Please amend the paragraph beginning on page 22, line 15 and ending on page 23, line 4 as follows:

As explained in the "Description of the Related Art", the resistance of the HGA against discharge currents, i.e., the ESD resistance of the HGA can be measured by using the device (charged device model; CDM) 17 shown by the circuit diagram in Fig. 15. Here, we let the potential difference between the conductive pattern 13 and the load beam 11 be V' , and represent the ESD withstand voltage V_d by the value of the minimum potential difference V' that causes damage to the MR element when one of pads 13a (open terminals) is connected to the ground after a potential difference V' is provided between the conductive pattern 13 and the load beam 11 by charging the conductive pattern 13. Then, the ESD withstand voltage V_d , for example, of a recent HGA is 3 V. Hence, if a metal makes contact with the pad in a state where

the potential difference V_h between the conductive pattern 13 and the load beam 11 in the HGA is over 3 V, the MR element will be ~~destroyed~~destroyed.